

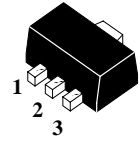
NPN EPITAXIAL PLANAR TRANSISTOR

(Pb) Lead(Pb)-Free

Description

The WTM1624 applies to voltage regulators, relay drivers, lamp drivers, and electrical equipment.

1. BASE
2. COLLECTOR
3. EMITTER


SOT-89
Features

- Adoption of FBET, MBIT processes
- Low collector-to-emitter saturation voltage
- Fast switching speed
- Large current capacity and wide ASO

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	Vcbo	60	V
Collector to Emitter Voltage	Vceo	50	V
Emitter to Base Voltage	Vebo	6	V
Collector Current (DC)	Ic	3	A
Collector Current (Pulse) (Note1)	Icp	6	A
Total Power Dissipation	Pd	0.5	W

Note 1: Single pulse, PW=10ms

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Electrical Characteristics (Ta = 25°C, unless otherwise stated)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVcbo	60	-	-	V	Ic=10uA, IE=0
BVceo	50	-	-	V	Ic=1mA, IB=0
BVebo	6	-	-	V	IE=10uA, Ic=0
Icbo	-	-	1	uA	Vcb=40V, IE=0
IEBO	-	-	1	uA	VEB=4V, Ic=0
*VCE(sat)	-	0.19	0.5	V	Ic=2A, IB=100mA
*VBE(sat)	-	0.94	1.2	V	Ic=2A, IB=100mA
*hFE	100	-	560		Vce=2V, Ic=100mA
ft	-	150	-	MHz	Vce=10V, Ic=50mA
Cob	-	25	-	pF	Vcb=10V, IE=0, f=1MHz
tstg	-	650	-	ns	See test circuit
tf	-	35	-	ns	

*Measured under pulse condition. Pulse width \leq 380fls, Duty Cycle \leq 2%

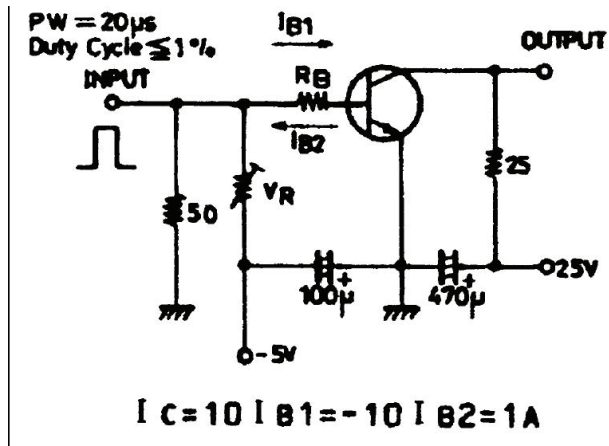
Classification of hFE

Rank	R	S	T	U
Range	100 - 200	140 - 280	200 - 400	280 - 560

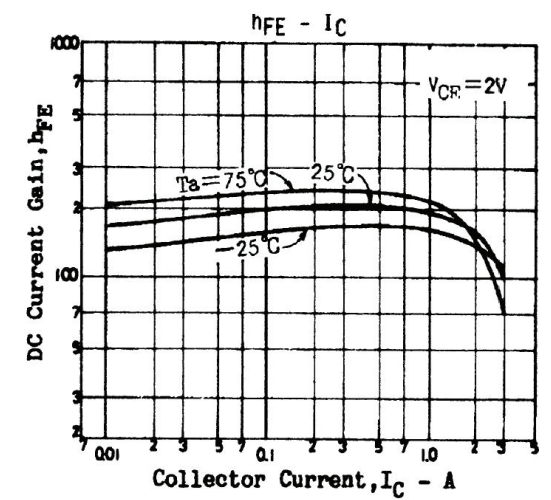
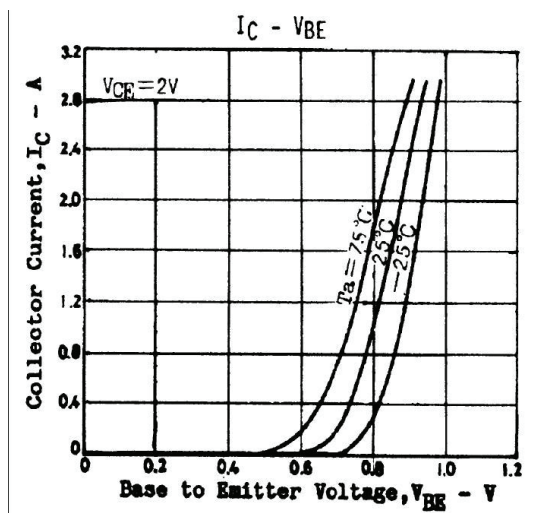
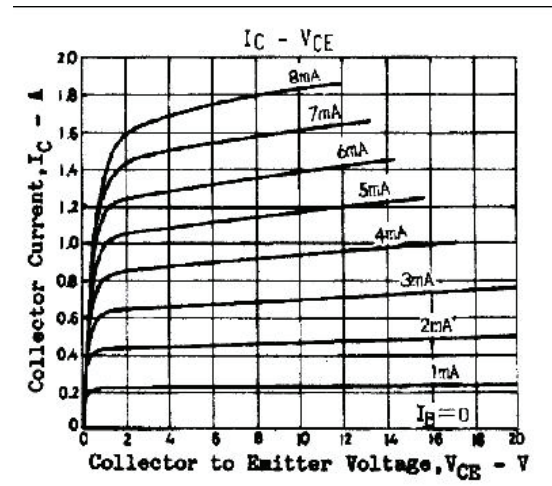
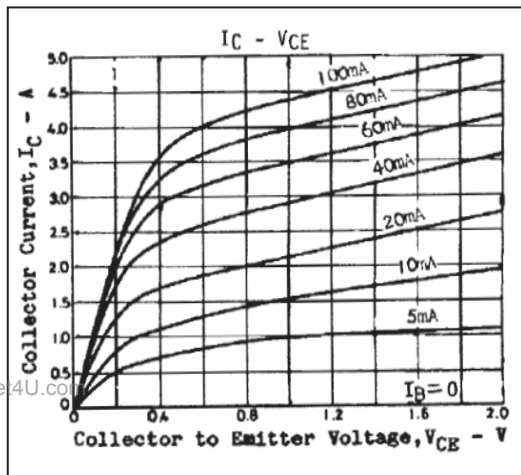
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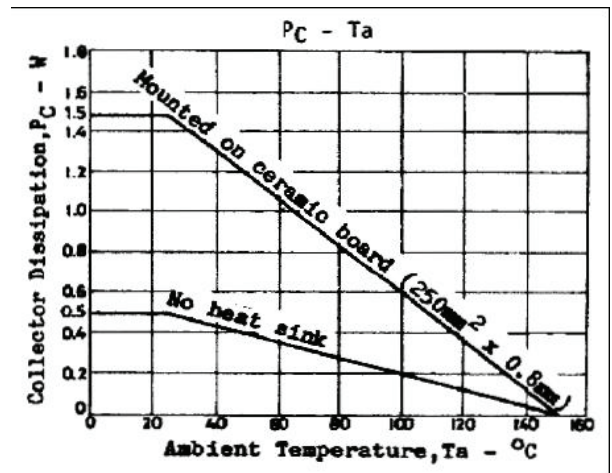
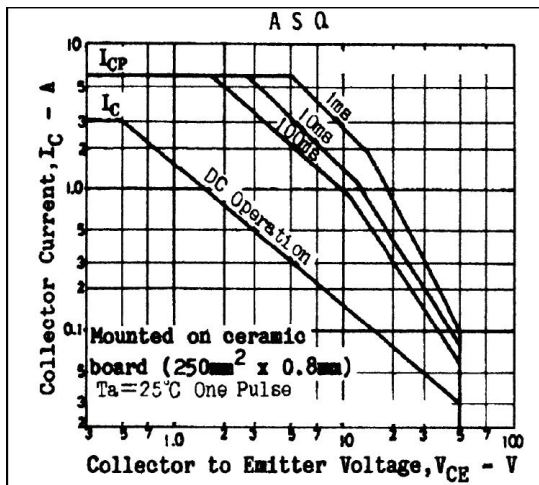
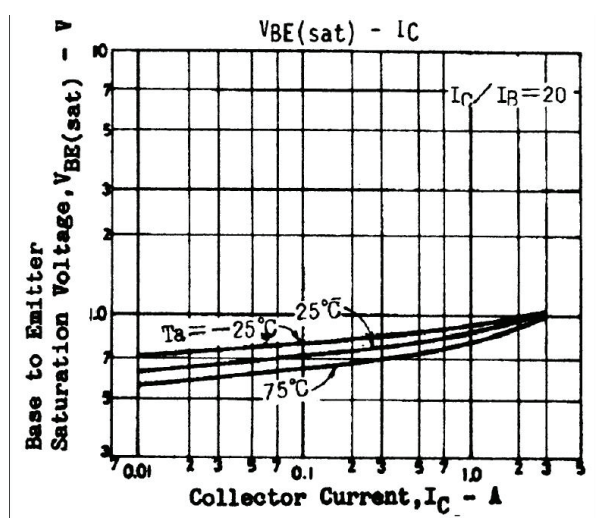
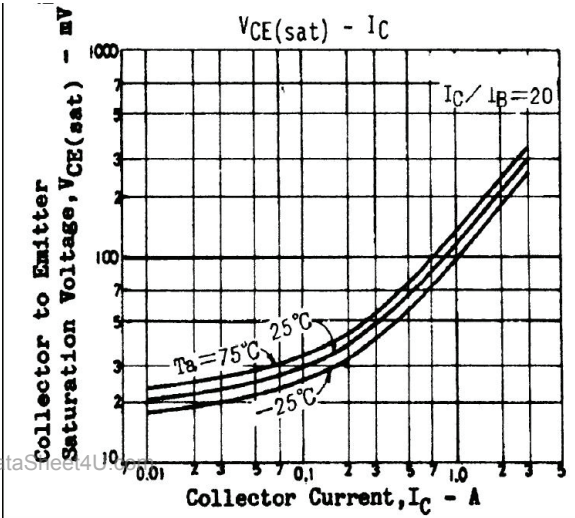
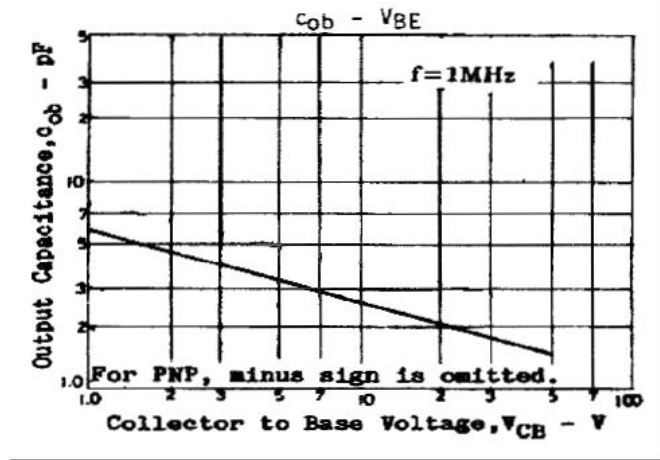
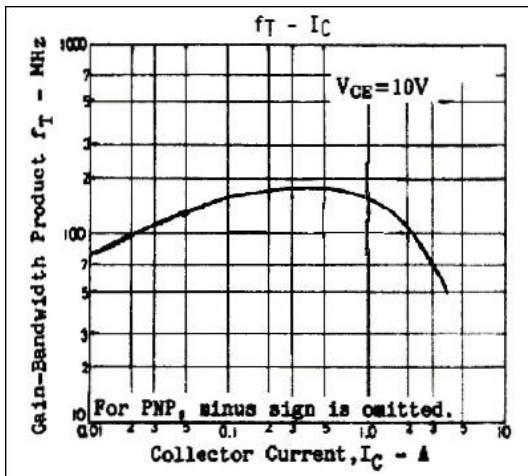
Test Circuit(Unit: resistance: Ω , capacitance: F)



Characteristics Curve

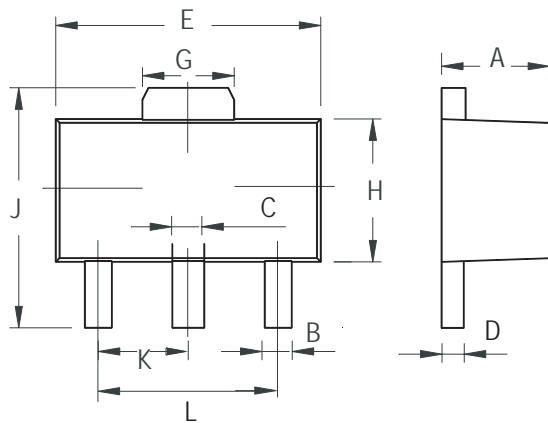


WTM1624



WTM1624**WEITRON****SOT-89 Outline Dimensions**

unit:mm



SOT-89		
Dim	Min	Max
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500TYP	
L	2.900	3.100